

## N-channel 600 V, 0.580 $\Omega$ typ., 5.5 A MDmesh II Plus™ low Qg Power MOSFET in a PowerFLAT™ 5x6 HV package

Datasheet - production data

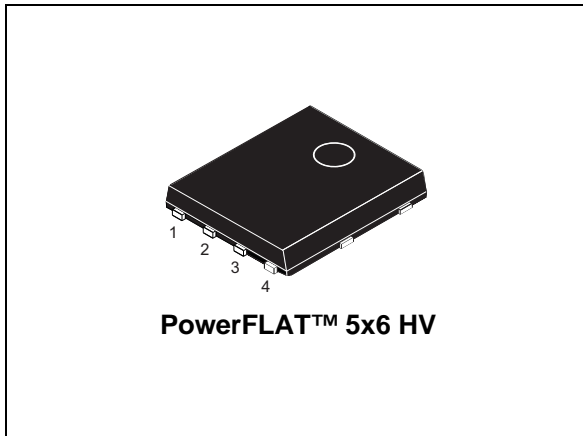
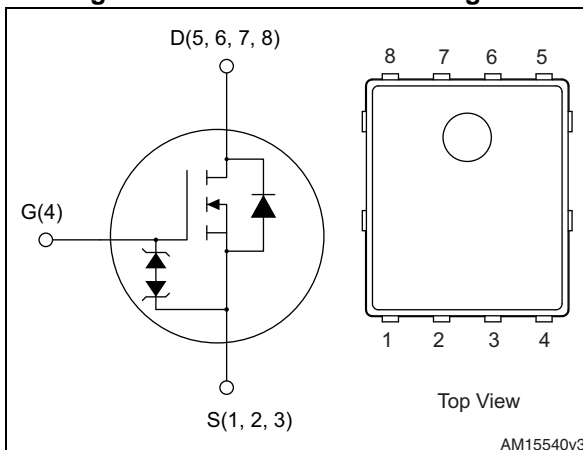


Figure 1. Internal schematic diagram



### Features

Order code	$V_{DS}$ @ $T_{Jmax}$	$R_{DS(on)}$ max	$I_D$
STL10N60M2	650 V	0.660 $\Omega$	5.5 A

- Extremely low gate charge
- Lower  $R_{DS(on)}$  x area vs previous generation
- Low gate input resistance
- 100% avalanche tested
- Zener-protected

### Applications

- Switching applications

### Description

This device is an N-channel Power MOSFET developed using a new generation of MDmesh™ technology: MDmesh II Plus™ low Qg. This revolutionary Power MOSFET associates a vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters.

Table 1. Device summary

Order code	Marking	Package	Packaging
STL10N60M2	10N60M2	PowerFLAT™ 5x6 HV	Tape and reel

# Contents

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{GS}$	Gate-source voltage	$\pm 25$	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ °C}$	5.5	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ °C}$	3.5	A
$I_{DM}^{(2)}$	Drain current (pulsed)	22	A
$P_{TOT}^{(2)}$	Total dissipation at $T_C = 25\text{ °C}$	48	W
$I_{AR}$	Avalanche current, repetitive or not-repetitive (pulse width limited by $T_j$ max)	1.5	A
$E_{AS}$	Single pulse avalanche energy (starting $T_j = 25\text{ °C}$ , $I_D = I_{AR}$ , $V_{DD} = 50\text{ V}$ )	110	mJ
$dv/dt^{(3)}$	Peak diode recovery voltage slope	15	V/ns
$dv/dt^{(4)}$	MOSFET $dv/dt$ ruggedness	50	V/ns
$T_{stg}$	Storage temperature	- 55 to 150	°C
$T_j$	Max. operating junction temperature	150	°C

1. The value is limited by package
2. Pulse width limited by safe operating area
3.  $I_{SD} \leq 5.5\text{ A}$ ,  $di/dt \leq 400\text{ A}/\mu\text{s}$ ,  $V_{DSpeak} \leq V_{(BR)DSS}$ ,  $V_{DD} = 80\% V_{(BR)DSS}$
4.  $V_{DS} \leq 480\text{ V}$

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	2.6	°C/W
$R_{thj-amb}^{(1)}$	Thermal resistance junction-amb max	59	°C/W

1. When mounted on 1inch<sup>2</sup> FR-4 board, 2 oz Cu

## 2 Electrical characteristics

( $T_C = 25\text{ °C}$  unless otherwise specified)

**Table 4. On /off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$ , $V_{GS} = 0$	600			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = 600\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 600\text{ V}$ , $T_C = 125\text{ °C}$			100	$\mu\text{A}$
$I_{GSS}$	Gate-body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 25\text{ V}$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$ , $I_D = 2.5\text{ A}$		0.580	0.660	$\Omega$

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 100\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0$	-	400	-	pF
$C_{oss}$	Output capacitance		-	22	-	pF
$C_{rss}$	Reverse transfer capacitance		-	0.84	-	pF
$C_{oss\text{ eq.}}^{(1)}$	Output equivalent capacitance	$V_{DS} = 0$ to $480\text{ V}$ , $V_{GS} = 0$	-	83	-	pF
$R_G$	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	6.4	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 480\text{ V}$ , $I_D = 7.5\text{ A}$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 15</a> )	-	13.5	-	nC
$Q_{gs}$	Gate-source charge		-	2.1	-	nC
$Q_{gd}$	Gate-drain charge		-	7.2	-	nC

1.  $C_{oss\text{ eq.}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DS}$ .

**Table 6. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}$ , $I_D = 3.75\text{ A}$ , $R_G = 4.7\text{ }\Omega$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 19</a> )	-	8.8	-	ns
$t_r$	Rise time		-	8	-	ns
$t_{d(off)}$	Turn-on delay time		-	32.5	-	ns
$t_f$	Fall time		-	13.2	-	ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		5.5	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		22	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 7.5 \text{ A}$ , $V_{GS} = 0$	-		1.6	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 7.5 \text{ A}$ , $di/dt = 100 \text{ A}/\mu\text{s}$	-	270		ns
$Q_{rr}$	Reverse recovery charge	$V_{DD} = 60 \text{ V}$ (see <a href="#">Figure 16</a> )	-	2		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	14.4		A
$t_{rr}$	Reverse recovery time	$V_{DD} = 60 \text{ V}$	-	376		ns
$Q_{rr}$	Reverse recovery charge	$di/dt = 100 \text{ A}/\mu\text{s}$ , $I_{SD} = 7.5 \text{ A}$	-	2.8		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current	$T_j = 150 \text{ }^\circ\text{C}$ (see <a href="#">Figure 16</a> )	-	15		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

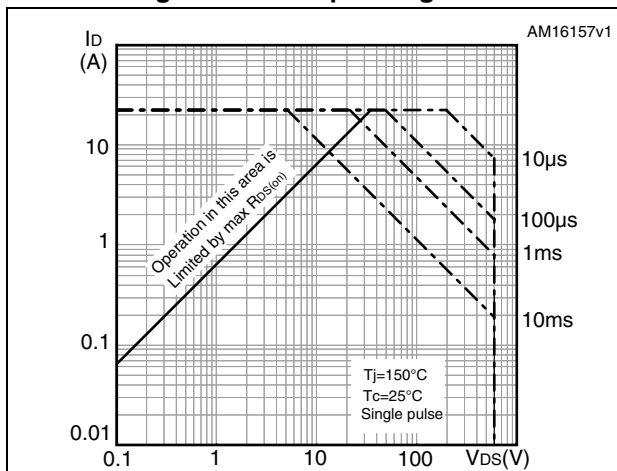


Figure 3. Thermal impedance

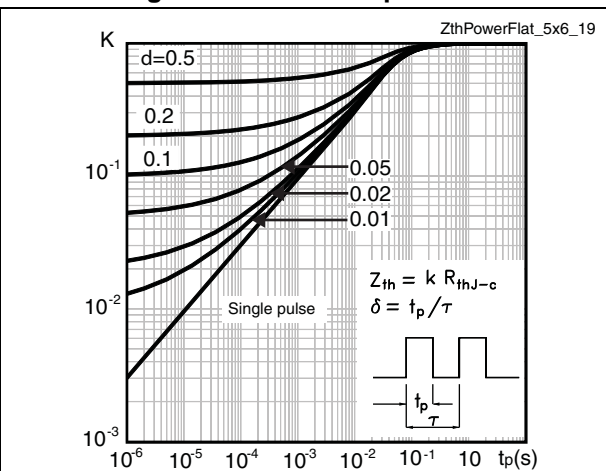


Figure 4. Output characteristics

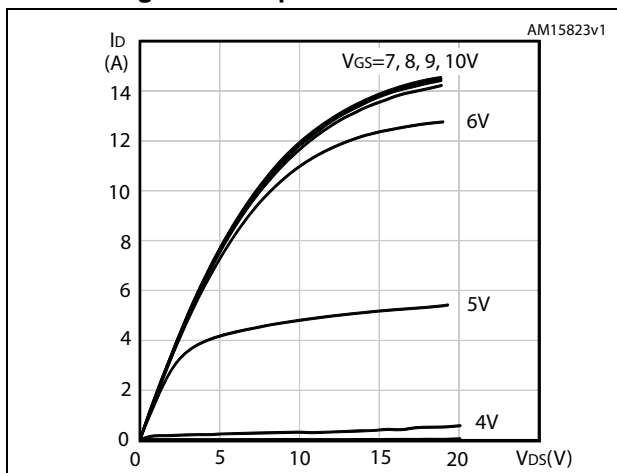


Figure 5. Transfer characteristics

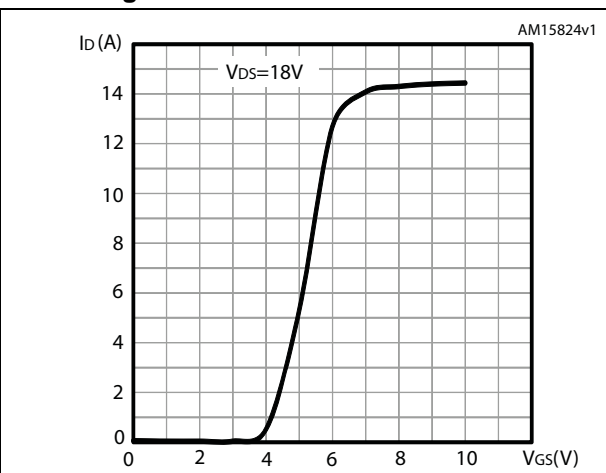


Figure 6. Gate charge vs gate-source voltage

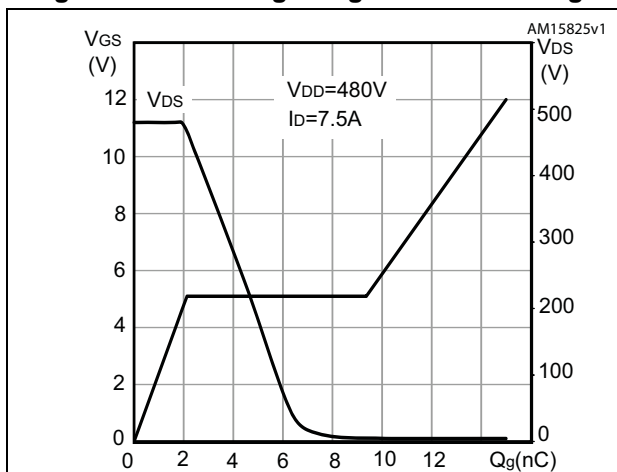


Figure 7. Static drain-source on-resistance

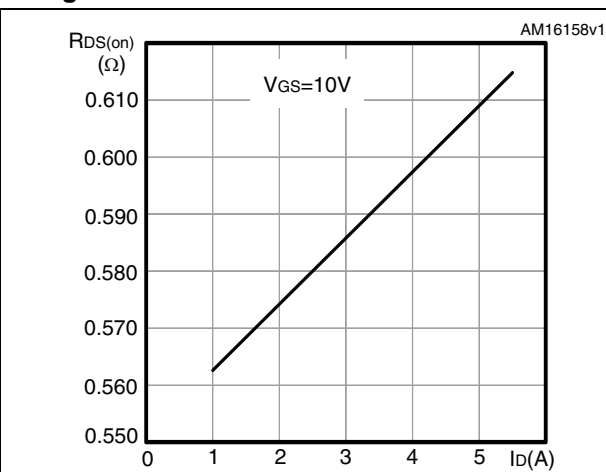


Figure 8. Capacitance variations

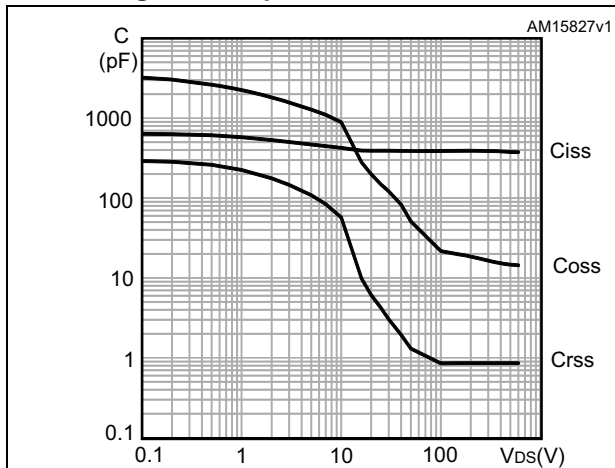


Figure 9. Output capacitance stored energy

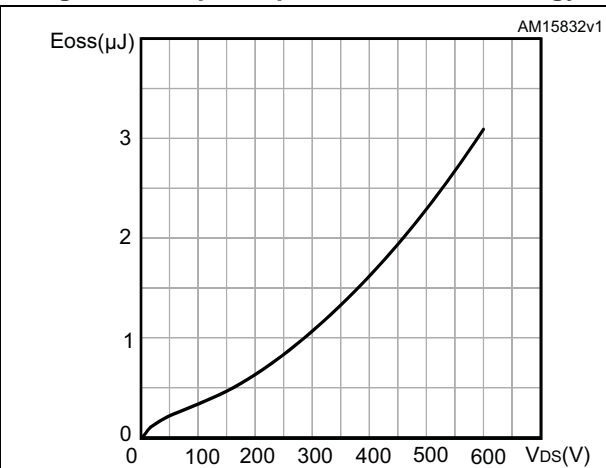


Figure 10. Normalized gate threshold voltage vs temperature

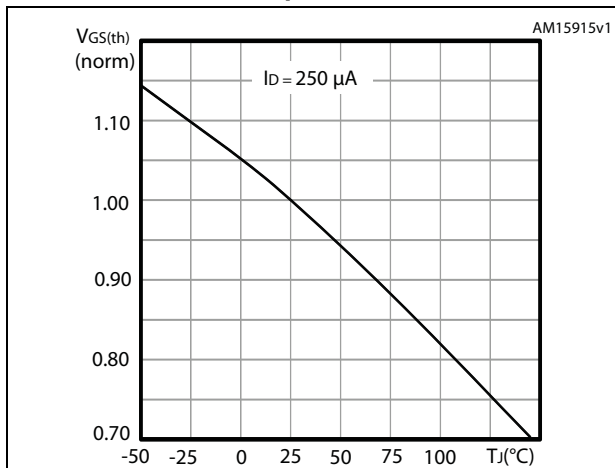


Figure 11. Normalized on-resistance vs temperature

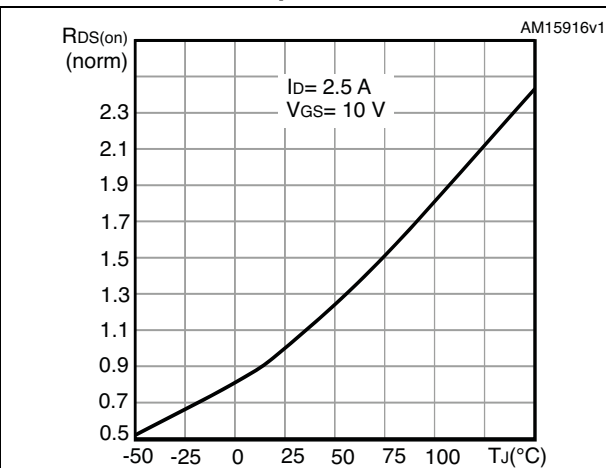


Figure 12. Normalized V(BR)DSS vs temperature

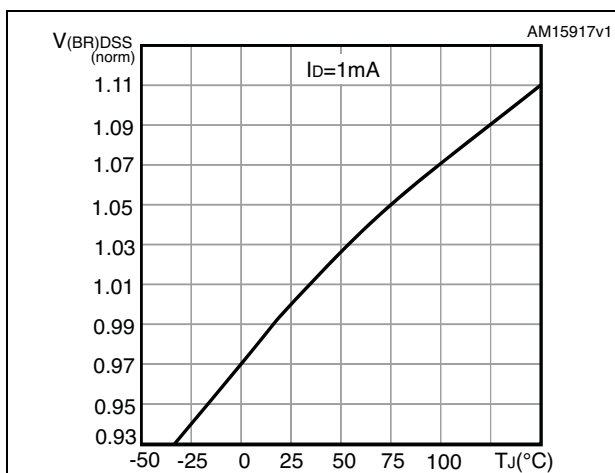
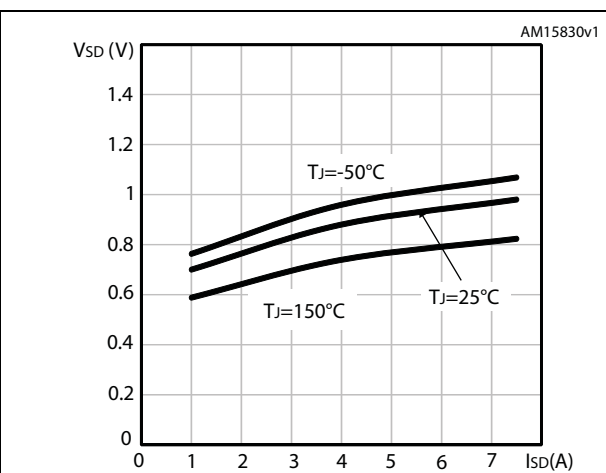
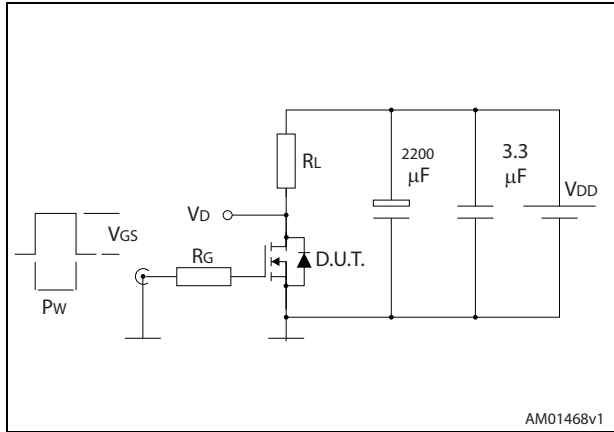


Figure 13. Source-drain diode forward characteristics



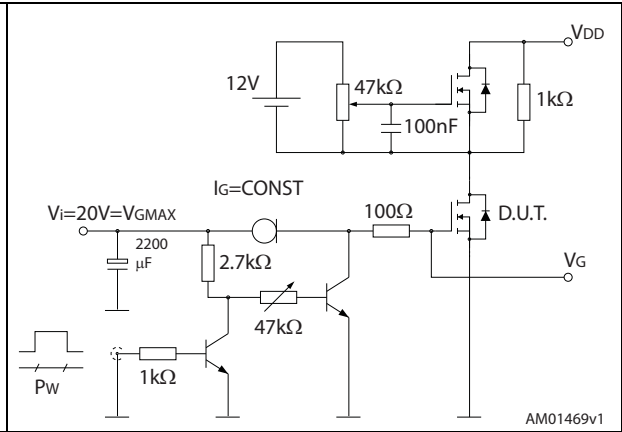
### 3 Test circuits

**Figure 14. Switching times test circuit for resistive load**



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**Figure 15. Gate charge test circuit**



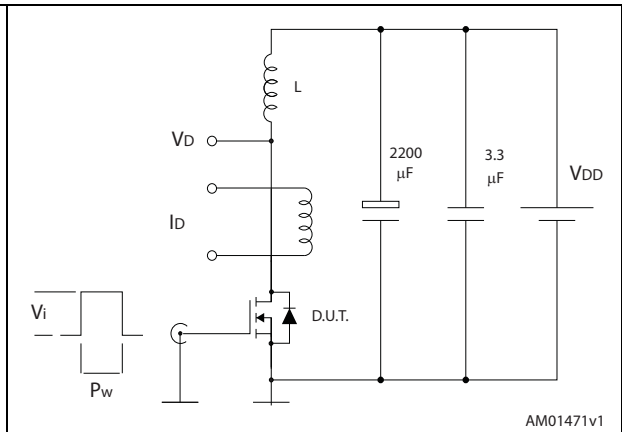
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**Figure 16. Test circuit for inductive load switching and diode recovery times**



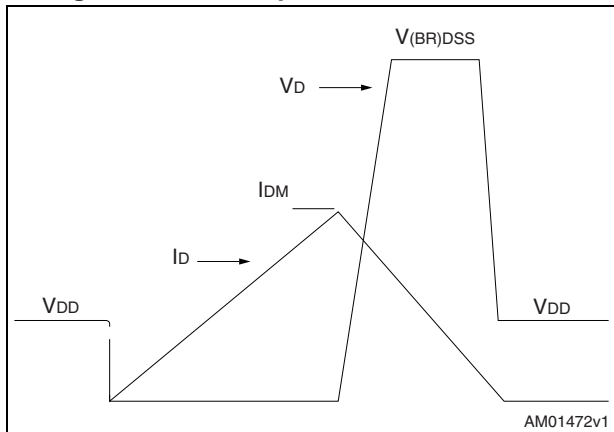
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**Figure 17. Unclamped inductive load test circuit**



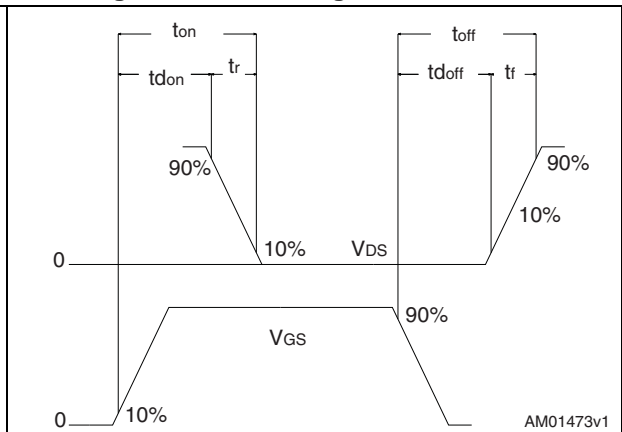
AM01471v1

**Figure 18. Unclamped inductive waveform**



AM01472v1

**Figure 19. Switching time waveform**



AM01473v1



## 4 Package mechanical data

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Figure 20. PowerFLAT™ 5x6 HV drawing

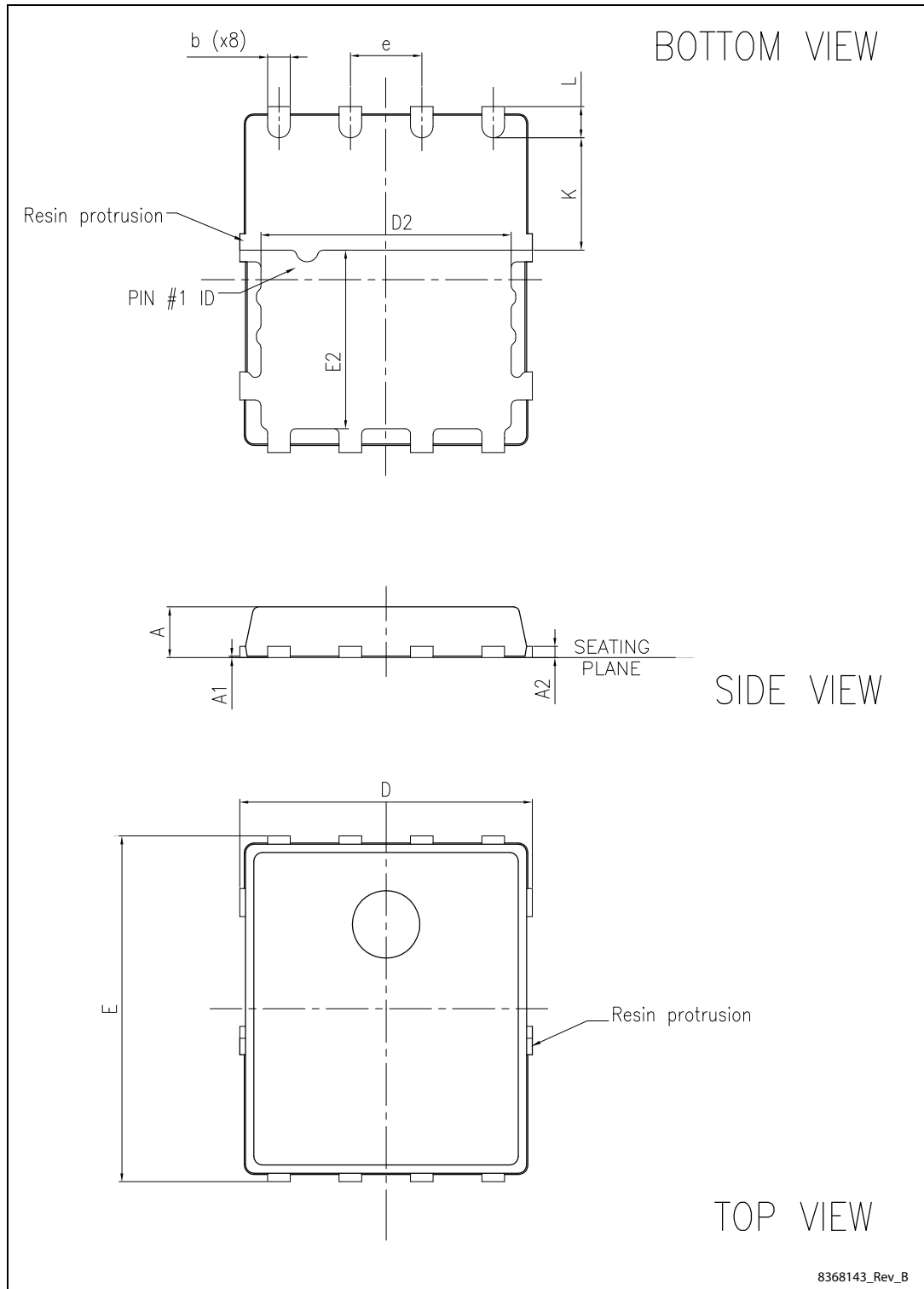
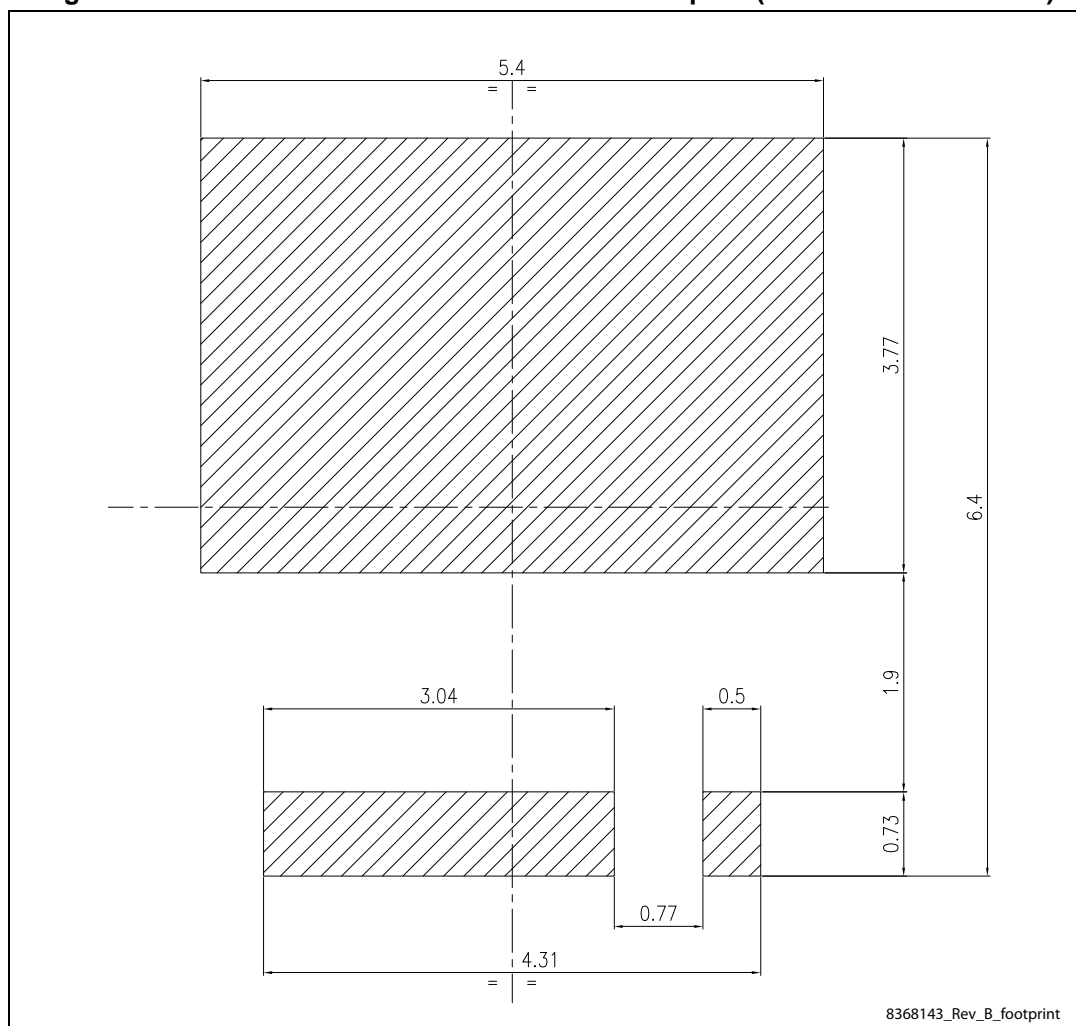


Table 8. PowerFLAT™ 5x6 HV mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80		1.00
A1	0.02		0.05
A2		0.25	
b	0.30		0.50
D	5.00	5.20	5.40
E	5.95	6.15	6.35
D2	4.30	4.40	4.50
E2	3.10	3.20	3.30
e		1.27	
L	0.50	0.55	0.60
K	1.90	2.00	2.10

Figure 21. PowerFLAT™ 5x6 HV recommended footprint (dimensions are in mm)



# 5 Packaging mechanical data

Figure 22. PowerFLAT™ 5x6 tape<sup>(a)</sup>

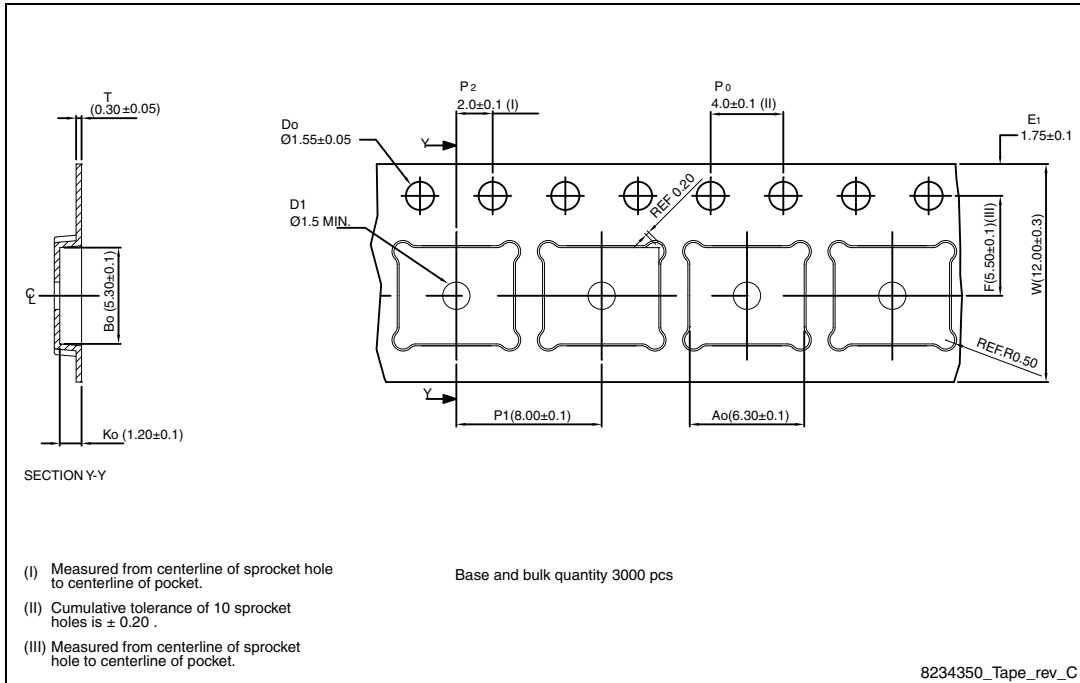
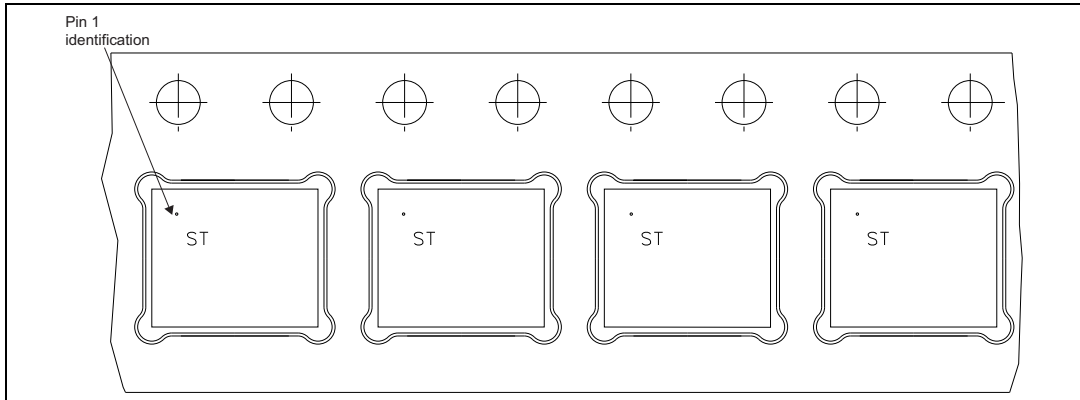
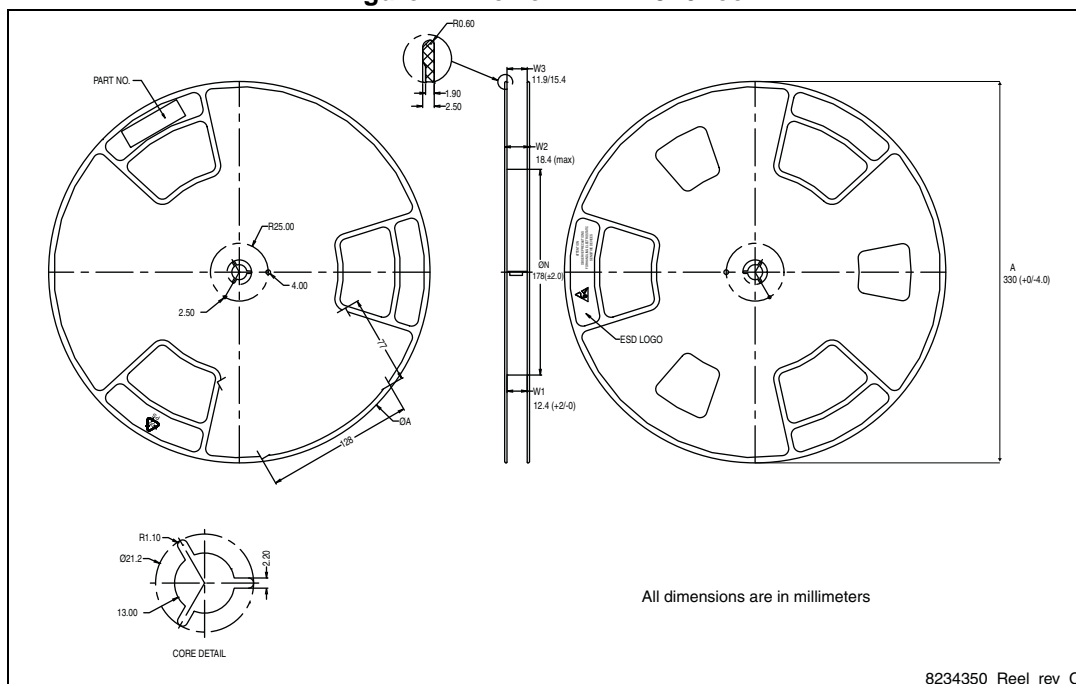


Figure 23. PowerFLAT™ 5x6 package orientation in carrier tape.



a. All dimensions are in millimeters.

Figure 24. PowerFLAT™ 5x6 reel



## 6 Revision history

**Table 9. Document revision history**

<b>Date</b>	<b>Revision</b>	<b>Changes</b>
28-Oct-2013	1	First release.
26-Mar-2014	2	Document status promoted from preliminary to production data. Minor text changes.

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